TOSHIBA Diode Silicon Epitaxial Schottky Barrier Type

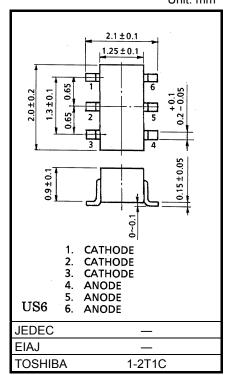
HN2S03FU

High Speed Switching Application

- HN2S03FU is composed of 3 independent diodes.
- Low forward voltage : V_{F (3)} = 0.50V (typ.)
- Low reverse current : I_R= 0.5µA (max)
- Small total capacitance : C_T = 3.9pF (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit	
Maximum (peak) reverse Voltage	V _{RM}	25	V	
Reverse voltage	V _R	20	V	
Maximum (peak) forward current	I _{FM}	100 *	mA	
Average forward current	Ι _Ο	50 *	mA	
Surge current (10ms)	I _{FSM}	1 *	А	
Power dissipation	Р	200 **	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T _{stg}	-55~125	°C	
Operating temperature range	T _{opr}	-40~110	°C	



Weight: 6.2mg(Typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

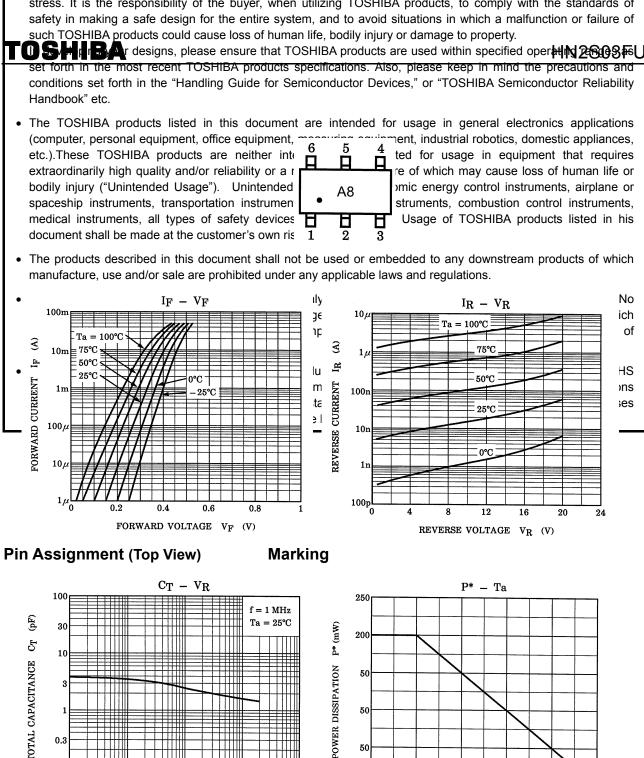
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

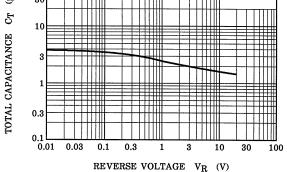
- * : This is absolute maximum rating of single diode (Q1 or Q2 or Q3). In the case of using 2 or 3 diodes, the absolute maximum ratings per diodes is 75 % of the single diode one.
- ** :Total rating

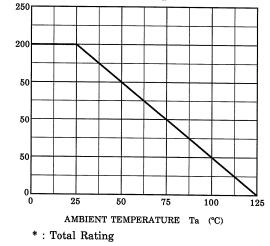
Electrical Characteristics (Q1, Q2, Q3 Common, Ta = 25°C)

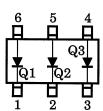
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Forward voltage	V _{F (1)}	_	I _F = 1mA		0.33	_	
	V _{F (2)}	-	I _F = 5mA	_	0.38	_	V
	V _{F (3)}	-	I _F = 50mA	_	0.50	0.55	
Reverse current	Ι _R	-	V _R = 20V	_	-	0.5	μA
Total capacitance	CT	_	V _R = 0, f = 1MH _z		3.9	_	pF

Unit: mm









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